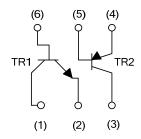


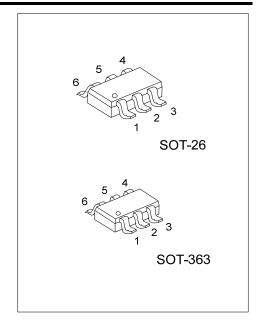
UNISONIC TECHNOLOGIES CO., LTD

IMZ2A DUAL TRANSISTOR

POWER MANAGEMENT (DUAL TRANSISTOR)

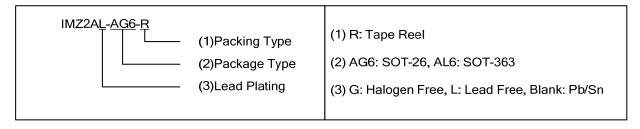
- **FEATURES**
- * Two a 9014 chip in a SMT package.
- **EQUIVALENT CIRCUITS**



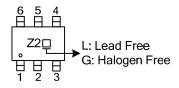


ORDERING INFORMATION

Ordering Number		Dookogo	Pin Assignment					Dooking		
Lead Free	Halogen Free	Package	1	2	3	4	5	6	Packing	
IMZ2AL-AG6-R	IMZ2AG-AG6-R	SOT-26	C1	E1	C2	E2	B2	B1	Tape Reel	
IMZ2AL-AL6-R	IMZ2AG-AL6-R	SOT-363	C1	E1	C2	E2	B2	B1	Tape Reel	



MARKING



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■ ABSOLUTE MAXIMUM RATINGS (T_A =25°C)

PARAMETER		SYMBOL	RATINGS	UNIT	
Callagton Book Voltage	TR1	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	60		
Collector-Base Voltage	TR2	V _{CBO}	-60	V	
O-II4 F:4 \/-4	TR1	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	50	V	
Collector-Emitter Voltage	TR2	V _{CEO}	-50		
Freitter Base Valters	TR1	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	7	V	
Emitter-Base Voltage	TR2	V_{EBO}	-6	V	
Calla eta e Curra et	TR1		150	A	
Collector Current	TR2	Ic	-150	mA	
O-Ht D Diiti (T-t-)	SOT-26	D-	300 (Note1)	\/	
Collector Power Dissipation (Total)	SOT-363	Pc	200	mW	
unction Temperature		TJ	+150	°C	
Storage Temperature		T _{STG}	-55~+150	°C	

Note: 1. 200mW per element must not be exceeded.

■ ELECTRICAL CHARACTERISTICS (T_A=25°C)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
TR1						
Collector-Base Breakdown Voltage	BV _{CBO}	I _C =50μA	60			V
Collector-Emitter Breakdown Voltage	BV _{CEO}	$I_C = 1mA$	50			V
Emitter-Base Breakdown Voltage	BV _{EBO}	I _E = 50μA	7			V
Collector Cut-Off Current	I _{CBO}	V _{CB} =60V			0.1	μΑ
Emitter Cut-Off Current	I _{EBO}	V _{EB} =7V			0.1	μΑ
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	$I_C / I_B = 50 \text{mA/5mA}$			0.4	V
DC Current Transfer Ratio	h _{FE}	V_{CE} = 6V, I_{C} = 1mA	120		560	
Transition Frequency	f⊤	V_{CE} =12V, I_{E} =-2mA, f =100MHz (Note)		180		MHz
Output Capacitance	Сов	V _{CB} = 12V, I _E =0A, f=1MHz		2	3.5	pF
TR2						
Collector-Base Breakdown Voltage	BV _{CBO}	$I_C = -50\mu A$	-60			V
Collector-Emitter Breakdown Voltage	BV_CEO	$I_C = -1mA$	-50			V
Emitter-Base Breakdown Voltage	BV_{EBO}	I _E = -50μA	-6			V
Collector Cut-Off Current	I _{CBO}	V _{CB} = -60V			-0.1	μΑ
Emitter Cut-Off Current	I _{EBO}	V _{EB} = -6V			-0.1	μΑ
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	$I_C / I_B = -50 \text{mA}/-5 \text{mA}$			-0.5	V
DC Current Transfer Ratio	h _{FE}	V_{CE} = -6V, I_{C} = -1mA	120		560	
Transition Frequency	f⊤	V _{CE} =-12V, I _E =2mA, f=100MHz (Note)		140		MHz
Output Capacitance	C _{OB}	V _{CB} = -12V,I _E =0A, f=1MHz		4	5	pF

Note: Transition frequency of the device.

^{2.} Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

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